

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

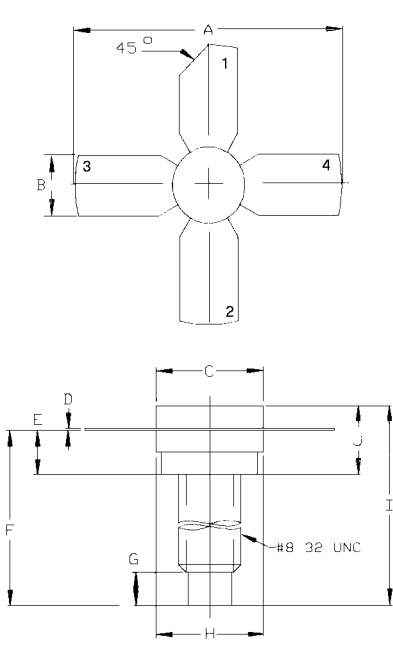
The **ASI TPV593** is a Common Emitter Device Designed for Class A High Linearity Television Band IV and V Transmitter Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- High Gain

MAXIMUM RATINGS

I_C	1.2 A
V_{CB}	45 V
P_{DISS}	17.5 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	10 °C/W

PACKAGE STYLE .280 4L STUD		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
	A	1.010/25,65
	B	.220/5,59
	C	.270/6,86
	D	.003/0,08
	E	.117/2,97
	F	.5/2/14,53
	G	.130/3,30
	H	.275/6,99
	I	.640/16,26
	J	.175/4,45
		.21/75,51

1 = COLLECTOR 2 = BASE
3 & 4 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 40 mA	26			V
BV_{CBO}	I _C = 10 mA	45			V
BV_{EBO}	I _E = 10 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 250 mA	10			---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz		8.0		pF
P_G	P _o = 2.0 W SOUND CARRIER = -10 dB VISION CARRIER = -8.0 dB CHROMA = 16 dB V _{CE} = 25 V I _C = 410 mA f = 860 MHz	10	12		dB
IMD₃	P _o = 2.0 W SOUND CARRIER = -10 dB VISION CARRIER = -8.0 dB CHROMA = 16 dB V _{CE} = 25 V I _C = 410 mA f = 860 MHz			-60	dBc